

**TOSHIBA**

**1SS293**

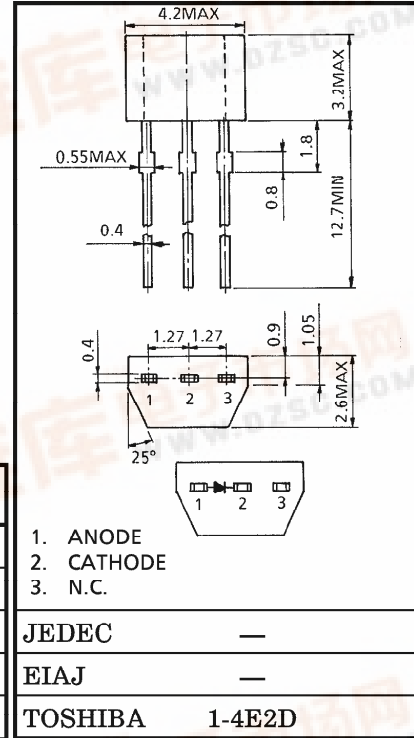
TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

# 1SS293

LOW VOLTAGE HIGH SPEED SWITCHING.

Unit in mm

- Low Forward Voltage :  $V_F(3) = 0.54V$  (Typ.)
- Low Reverse Current :  $I_R = 5\mu A$  (Max.)
- Small Package



MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	$V_{RM}$	45	V
Reverse Voltage	$V_R$	40	V
Maximum (Peak) Forward Current	$I_{FM}$	300	mA
Average Forward Current	$I_O$	100	mA
Power Dissipation	P	300	mW
Junction Temperature	$T_j$	125	°C
Storage Temperature Range	$T_{stg}$	-55~125	°C

JEDEC	—
EIAJ	—
TOSHIBA	1-4E2D

Weight : 0.13g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_F(1)$	$I_F = 1mA$	—	0.28	—	V
	$V_F(2)$	$I_F = 10mA$	—	0.36	—	
	$V_F(3)$	$I_F = 100mA$	—	0.54	0.60	
Reverse Current	$I_R$	$V_R = 40V$	—	—	5	$\mu A$
Total Capacitance	$C_T$	$V_R = 0, f = 1MHz$	—	18	25	pF

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